

JMY1852P

Product Preview

12V 12A P-Channel MOSFET



Features

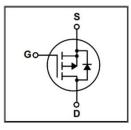
- Advanced trench technology
- Ultra-low on-resistance
- RoHS compliant

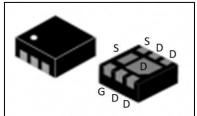


Product Summary				
V _{DS} -12V				
	9.5mΩ (Typ.)			
R _{DS(ON)}	12.3mΩ (Max.)			
I _D	-12A			

Applications

- Motor controllers
- DC-to-DC convertors
- Battery-driven electronic products, electrical equipment and machines





Ordering Information

Part Number	Marking	Package	Packaging
JMY1852P	Y1852P	DFN2x2	Tape & Reel



Absolute Maximum Ratings

Parameter	Symbol	Limit	Unit
Drain-to-Source Voltage	V_{DS}	-12	V
Gate-to-Source Voltage	V_{GS}	±12	V
Continuous Drain Current, Package Limited (T _C = 25°C) ⁽¹⁾	I _D	-12	
Continuous Drain Current, Silicon Limited (T _C = 25°C) ⁽¹⁾	I _D	-37	
Continuous Drain Current, Silicon Limited (T _C = 100°C) (1)	I _D	-23	
Continuous Drain Current, Silicon Limited t (T _A = 25°C) (2), (5)	I _D	-9	Α
Continuous Drain Current , Silicon Limited (T _A = 100°C) (2), (5)	I _D	-6	
Pulsed Drain Current (3)	I _{DM}	-48	
Power Dissipation (T _C = 25°C)	P _D	30.5	W
Linear Derating Factor	-	0.24	W/°C
Single Pulse Avalanche Energy (4)	E _{AS}	17	mJ
Avalanche Current	I _{AS}	13	Α
Junction Temperature	TJ	-55 to 150	°C
Storage Temperature	T _{STG}	-55 to 150	

Thermal Characteristics

Parameter	Symbol	Max	Unit
Junction-to-Ambient Thermal Resistance (5)	$R_{\theta JA}$	62	°C /\\
Junction-to-Case Thermal Resistance	$R_{ heta JC}$	4.1	°C/W

Static Electrical Characteristics (6)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-12	-	-	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}$, $I_{D} = -250 \mu A$	-0.5	-	-0.9	V
Drain-to-Source Leakage Current	I _{DSS}	$V_{DS} = -12V, V_{GS} = 0V$	-	-	-1	μΑ
Gate-to-Source Leakage Current	I _{GSS}	$V_{DS} = 0V, V_{GS} = \pm 12V$	-	-	±100	nA
Drain-to-Source On-Resistance	D	$V_{GS} = -4.5V$, $I_{D} = -8A$	-	9.5	12.3	mΩ
Diani-to-source Off-Resistance	R _{DS(ON)}	$V_{GS} = -2.5V$, $I_D = -8A$	-	13.5	17.5	mΩ



Dynamic Electrical Characteristics (6)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Forward Transconductance	g _{fs}	$V_{DS} = -5V, I_{D} = -10A$	-	60	-	S
Total Gate Charge	Q _g	V _{GS} = -4.5V,	-	20	-	
Gate-to-Source Charge	Q_{gs}	V _{DS} = -6V,	-	2	-	nC
Gate-to-Drain Charge	Q_{gd}	I _D = -8A	-	6	-	
Turn-On Delay Time	t _{d(on)}	V _{GS} = -4.5V,	-	15	-	
Rise Time	t _r	V _{DS} = -6V,	-	25	-	
Turn-Off Delay Time	t _{d(off)}	I _D = -8A,	-	70	-	ns
Fall Time	t _f	$R_G = 3.0\Omega$	-	45	-	
Input Capacitance	C _{iss}	V _{GS} = 0V,	-	2200	-	
Output Capacitance	C _{oss}	f = 200kHz,	-	400	-	pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = -6V	-	300	-	

Diode Characteristics (6)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = -8A$	-	-0.8	-	V
Reverse Recovery Time	t _{rr}	$V_{GS} = 0V$, $I_S = -5A$,	-	50	-	ns
Reverse Recovery Charge	Q _{rr}	$dI_s/dt = -100A/\mu s$	-	5	-	nC

- (1) Rated according to $R_{\theta \text{JC}}.$
- (2) Rated according to $R_{\theta JA}. \label{eq:Relation}$
- (3) Limited by maximum T_J .
- (4) $T_A = 25$ °C, L = 0.1mH, $I_{AS} = 13$ A.
- (5) Surface–mounted on 1 inch² FR4 board, 2 oz Cu.
- (6) $T_J = 25$ °C unless otherwise specified.

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Typical Electrical Characteristics

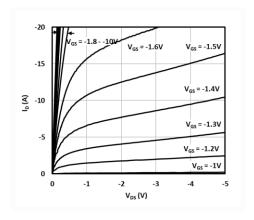


Fig. 1 Output characteristics

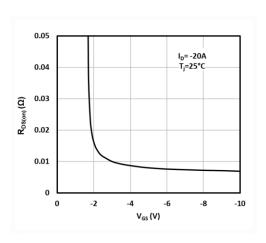


Fig.3 On-resistance vs. gate voltage

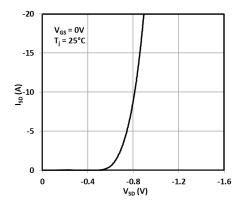


Fig.5 Source-to-drain diode forward characteristics

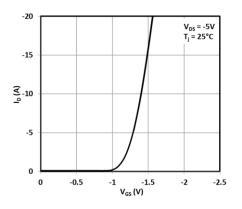


Fig. 2 Transfer characteristics

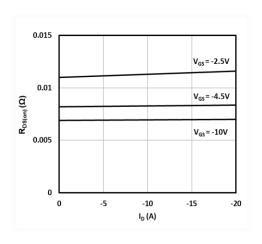


Fig.4 On-resistance vs. drain current

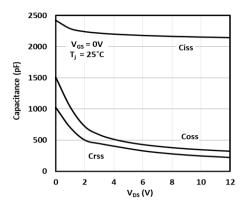


Fig.6 Capacitance vs. drain-to-source voltage



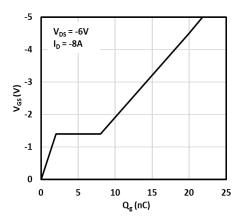


Fig.7 Gate-to-source voltage vs. gate charge

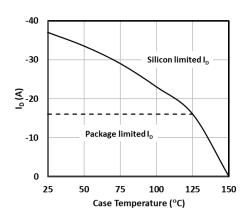


Fig.8 Maximum drain current vs. case temperature

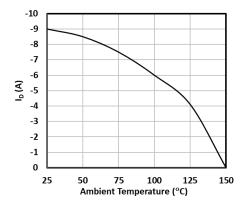
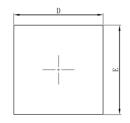
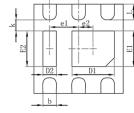


Fig. 9 Maximum drain current vs. ambient temperature

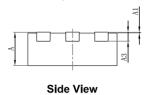


Package Drawing





Top View

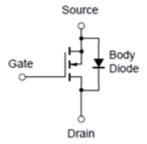


Bottom View

Symbol	Dimensions I	n Millimeters	Dimensions In Inches	
Syllibol	Min.	Max.	Min.	Max.
Α	0.700/0.800	0.800/0.900	0.028/0.032	0.032/0.035
A1	0.000	0.050	0.000	0.002
A3	0.203	REF.	0.008	REF.
D	1.924	2.076	0.076	0.082
Е	1.924	2.076	0.076	0.082
D1	0.850	1.050	0.033	0.041
E1	0.700	0.900	0.028	0.035
D2	0.200	0.400	0.008	0.016
E2	0.700	0.900	0.028	0.035
e1	0.650TYP.		0.026	STYP.
e2	0.325TYP.		0.013	STYP.
k	0.200	MIN.	0.008MIN.	
b	0.250	0.350	0.010	0.014
е	0.650	TYP.	0.026TYP.	
L	0.300	0.400	0.012	0.016

DFN 2x2

Equivalent Circuit





Revision history of JMY1852P specification

Version	Change Items	Effective Date
1.00	Initial Release	28-Feb-20



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